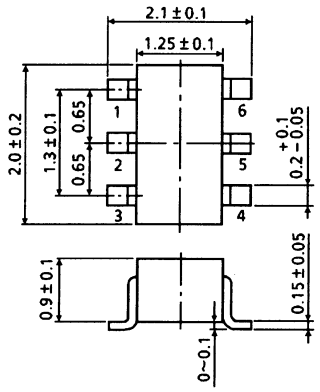
TOSHIBA Multi Chip Discrete Device

HN7G02FU

Power Management Switch Application, Inverter Circuit Application, Driver Circuit Application and Interface Circuit Application.

Q1 (transistor): RN2110 Equivalent
Q2 (MOS-FET): 2SK1830 Equivalent

Unit: mm



1. EMITTER
2. BASE
3. DRAIN
4. SOURCE
5. GATE
6. COLLECTOR

US6

JEDEC	—
JEITA	—
TOSHIBA	—

Weight: g (typ.)

Q1 (Transistor) Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	−50	V
Collector-emitter voltage	V_{CEO}	−50	V
Emitter-base voltage	V_{EBO}	−5	V
Collector current	I_C	−100	mA

Q2 (MOS-FET) Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DS}	20	V
Gate-source voltage	V_{GSS}	10	V
DC drain current	I_D	50	mA

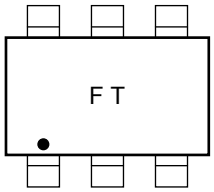
Q1, Q2 Common Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector power dissipation	P_C (Note 1)	200	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	−55~150	°C

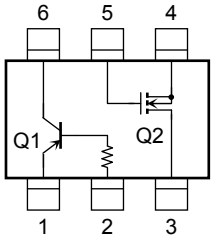
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Total rating

Marking



Equivalent Circuit (top view)



Q1 (Transistor) Electrical Characteristics (Ta = 25°C)

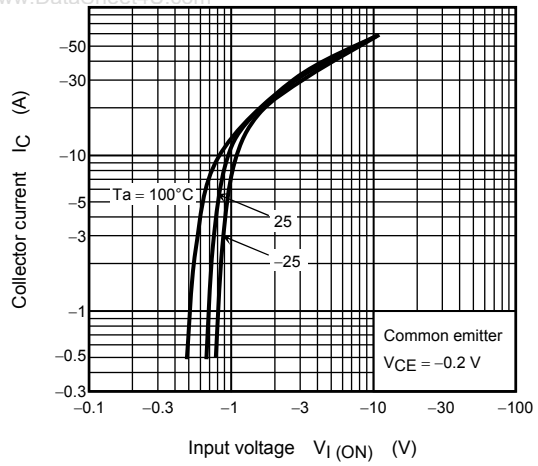
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = −50 V, I_E = 0	—	—	−100	nA
Emitter cut-off current	I_{EBO}	V_{EB} = −5 V, I_C = 0	—	—	−100	nA
DC current gain	h_{FE}	V_{CE} = −5 V, I_C = −1 mA	120	—	400	
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C = 5 mA, I_B = −0.25 mA	—	−0.1	−0.3	V
Input resistor	R1	—	3.29	4.7	6.11	kΩ

Q2 (MOS-FET) Electrical Characteristics (Ta = 25°C)

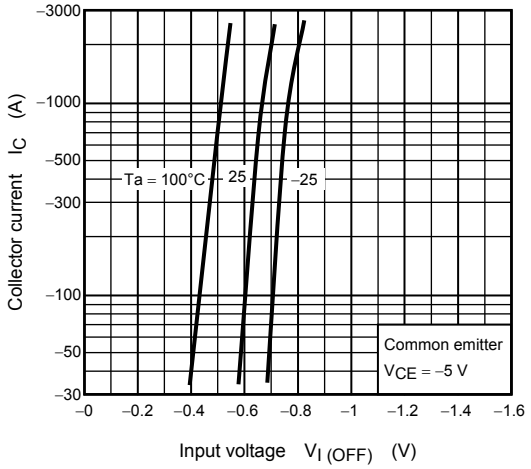
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	V_{GS} = 10 V, V_{DS} = 0	—	—	1	μA
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	I_D = 100 μA, V_{GS} = 0	20	—	—	V
Drain cut-off current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0	—	—	1	μA
Gate threshold voltage	V_{th}	V_{DS} = 3 V, I_D = 0.1 mA	0.5	—	1.5	V
Forward transfer admittance	$\|Y_{fs}\|$	V_{DS} = 3 V, I_D = 10 mA	20	—	—	mS
Drain-source ON resistance	$R_{DS\ (ON)}$	I_D = 10 mA V_{GS} = 2.5 V	—	20	40	Ω

Q1 (Transistor)

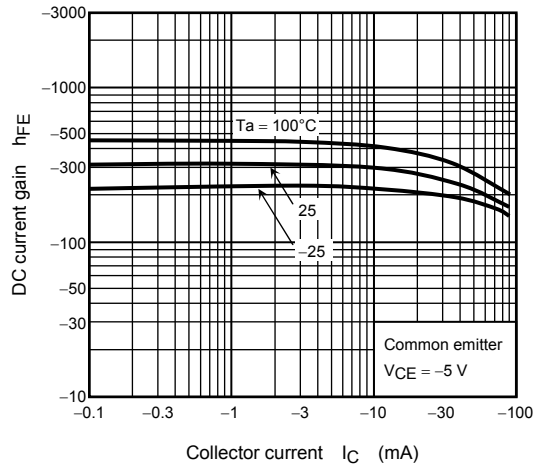
$I_C - V_{I\ (ON)}$



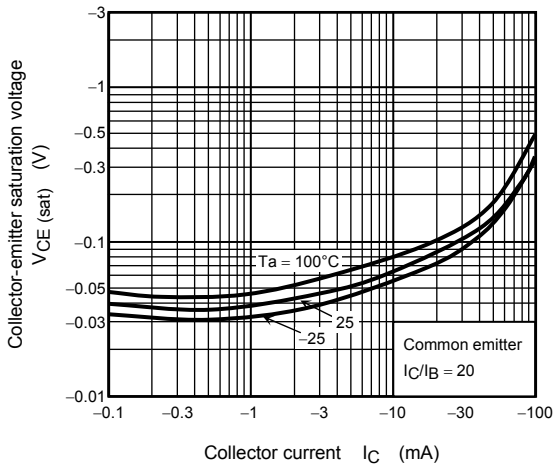
$I_C - V_{I\ (OFF)}$



$h_{FE} - I_C$

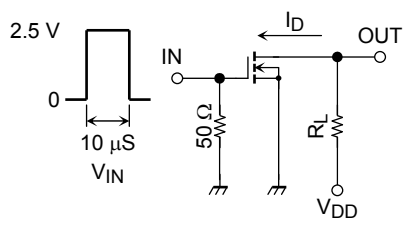


$V_{CE\ (sat)} - I_C$



Q2 (MOS-FET)

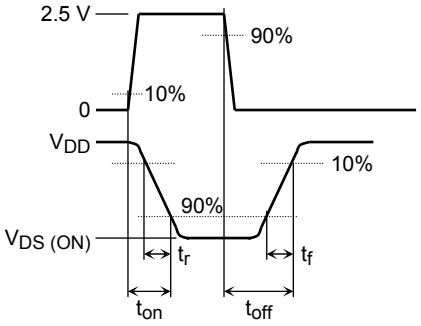
(a) Switching time test circuit



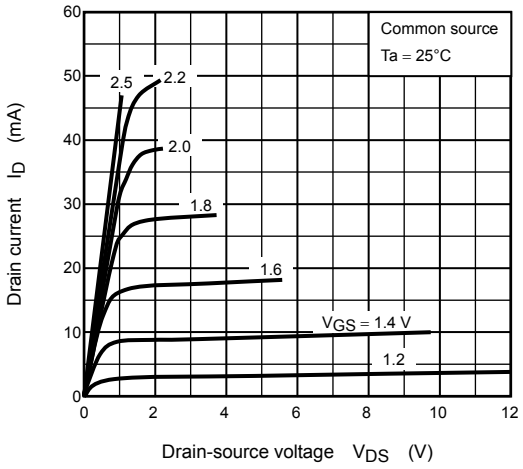
V_{DD} = 3 V
D.U. ≦ 1%
V_{IN}: t_r, t_f < 5 ns
(Z_{out} = 50 Ω)
Common source
Ta = 25°C

(b) V_{IN}
V_{GS}

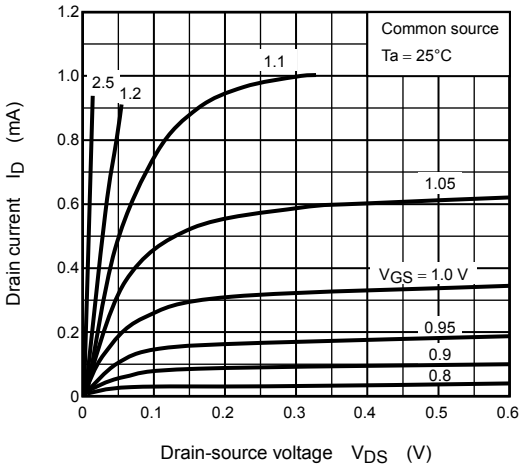
(c) V_{OUT}
V_{DS}



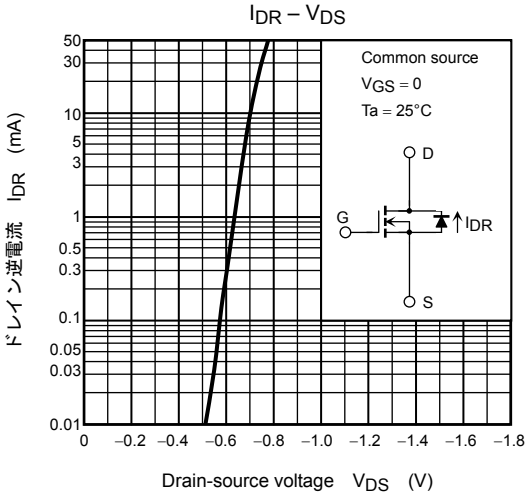
I_D – V_{DS}



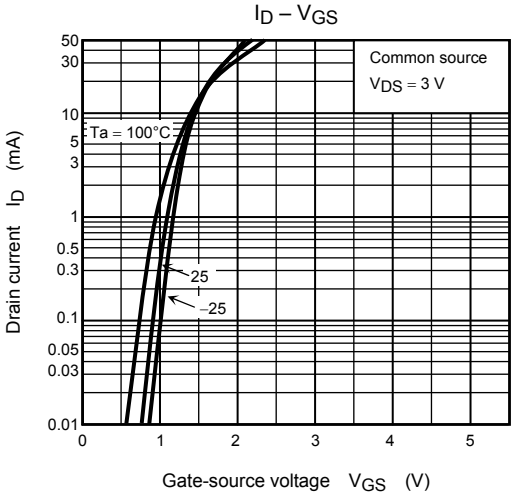
I_D – V_{DS} (低電圧領域)



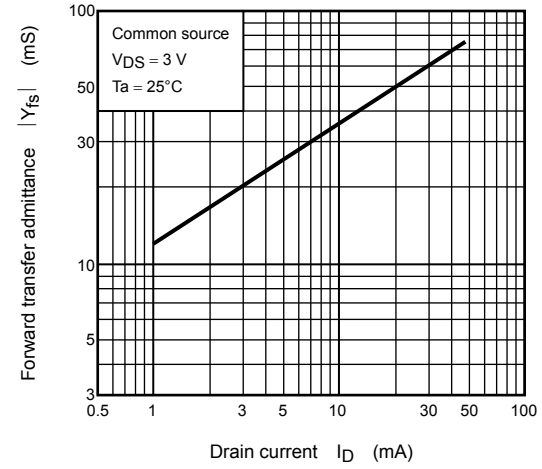
I_{DR} – V_{DS}



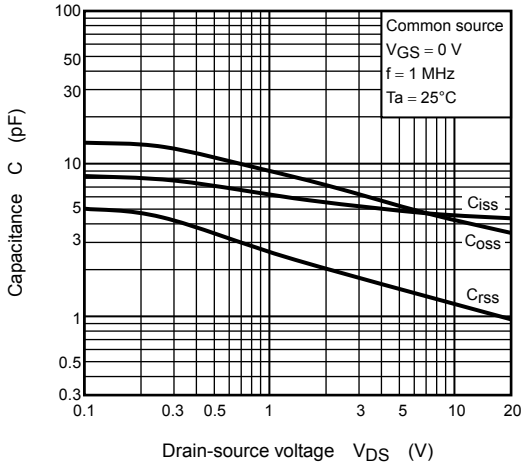
I_D – V_{GS}



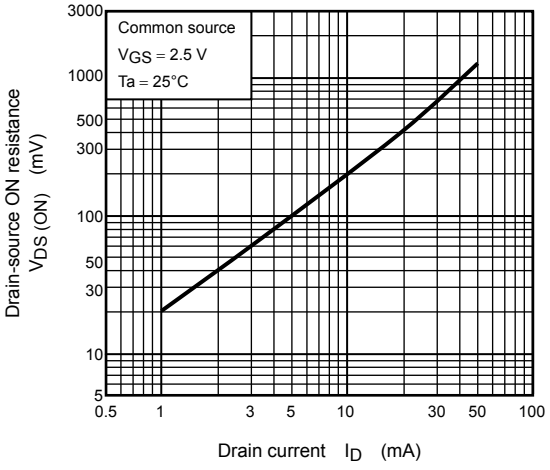
$|Y_{fs}| - I_D$



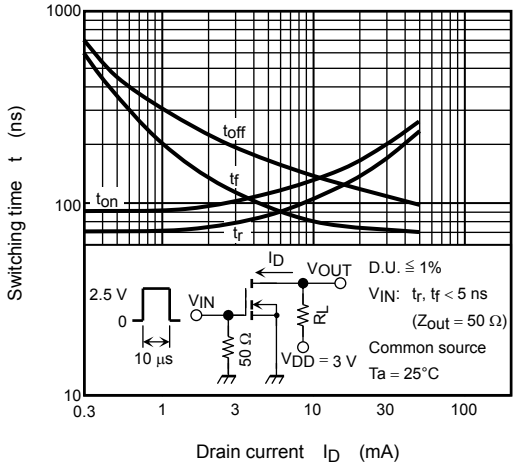
$C - V_{DS}$



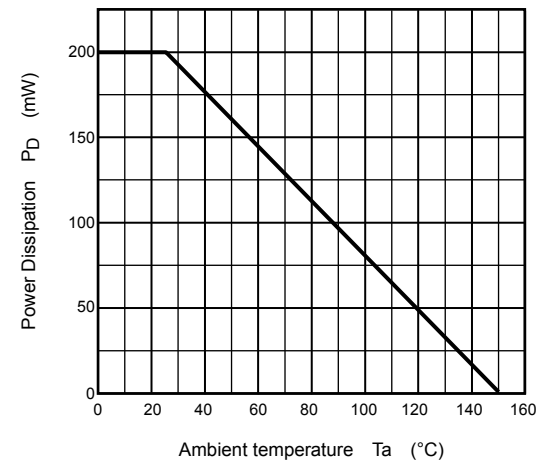
$V_{DS\ (ON)} - I_D$



$t - I_D$



$P_D - Ta$



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20070701-EN GENERAL

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